

BD675A/677A/679A/681

Medium Power Linear and Switching Applications

- Medium Power Darlington TR
- Complement to BD676A, BD678A, BD680A and BD682 respectively



NPN Epitaxial Silicon Transistor

Absolute Maximum Ratings T_C=25°C unless otherwise noted

Symbol	Parameter		Value	Units	
V _{CBO}	Collector-Base Voltage	: BD675A	45	V	
		: BD677A	60	V	
		: BD679A	80	V	
		: BD681	100	V	
V _{CEO}	Collector-Emitter Voltage	: BD675A	45	V	
		: BD677A	60	V	
		: BD679A	80	V	
		: BD681	100	V	
V _{EBO}	Emitter-Base Voltage		5	V	
I _C	Collector Current (DC)	4	Α		
I _{CP}	*Collector Current (Pulse)		6	Α	
I _B	Base Current		100	mA	
P _C	Collector Dissipation (T _C =25°C)		40	W	
T _J	Junction Temperature		150	°C	
T _{STG}	Storage Temperature		- 65 ~ 150	°C	

Electrical Characteristics $T_C=25$ °C unless otherwise noted

Symbol	Param	eter	Test Condition	Min.	Тур.	Max.	Units
V _{CEO} (sus)	*Collector-Emitter Sustaining Voltage						
		: BD675A	$I_C = 50 \text{mA}, I_B = 0$	45			V
		: BD677A		60			V
		: BD679A		80			V
		: BD681		100			V
I _{CBO}	Collector-Base Voltage	: BD675A	$V_{CB} = 45V, I_{E} = 0$			200	μΑ
		: BD677A	$V_{CB} = 60V, I_{E} = 0$			200	μΑ
		: BD679A	$V_{CB} = 80V, I_{E} = 0$			200	μΑ
		: BD681	$V_{CB} = 100V, V_{BE} = 0$			200	μΑ
I _{CEO}	Collector Cut-off Current	: BD675A	$V_{CE} = 45V, V_{BE} = 0$			500	μΑ
		: BD677A	$V_{CE} = 60V, V_{BE} = 0$			500	μΑ
		: BD679A	$V_{CE} = 80V, V_{BE} = 0$			500	μΑ
		: BD681	$V_{CE} = 100V, V_{BE} = 0$			500	μΑ
I _{EBO}	Emitter Cut-off Current		$V_{EB} = 5V, I_{C} = 0$			2	mA
h _{FE}	* DC Current Gain	: BD675A/677A/679A	$V_{CE} = 3V, I_{C} = 2A$	750			
		: BD681	$V_{CE} = 3V, I_{C} = 1.5A$	750			
V _{CE} (sat)	* Collector-Emitter Saturation Voltage						
		: BD675A/677A/679A	$I_C = 2A, I_B = 40mA$			2.8	V
		: BD681	$I_C = 1.5A, I_B = 30mA$			2.5	V
V _{BE} (on)	* Base-Emitter ON Voltage	e : BD675A/677A/679A	$V_{CE} = 3V, I_{C} = 2A$			2.5	V
		: BD681	$V_{CF} = 3V, I_{C} = 1.5A$			2.5	V

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Typical Characteristics

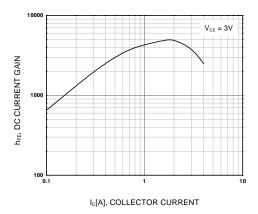


Figure 1. DC current Gain

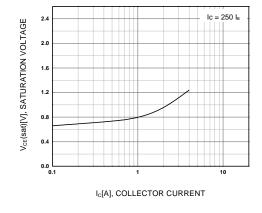


Figure 2. Collector-Emitter Saturation Voltage

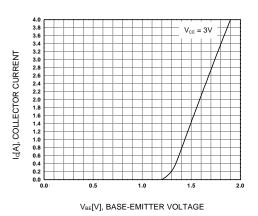


Figure 3. Base-Emitter On Voltage

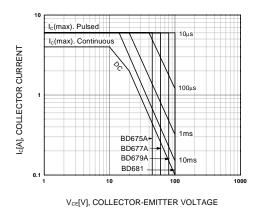


Figure 4. Safe Operating Area

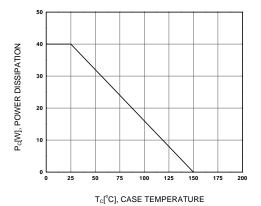
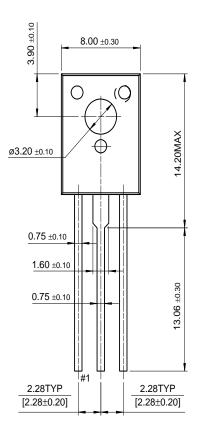


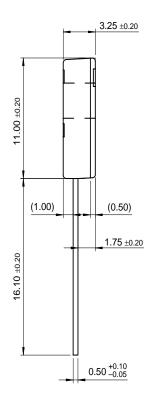
Figure 5. Power Derating

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Package Demensions

TO-126





Dimensions in Millimeters

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